

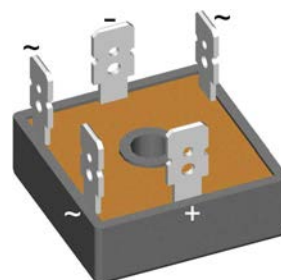
Standard Rectifier Module

3~ Rectifier	
V_{RRM}	= 1200 V
I_{DAV}	= 20 A
I_{FSM}	= 380 A

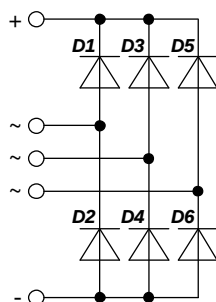
3~ Rectifier Bridge

Part number

VUO25-12NO8



 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: FO-B

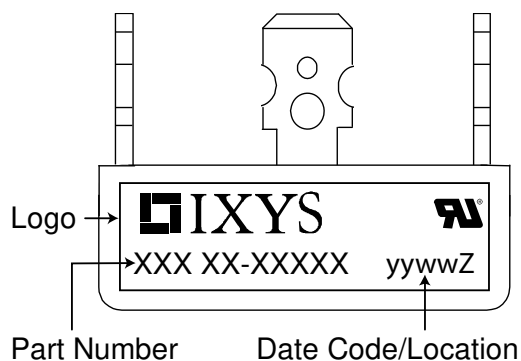
- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- 1/4" fast-on terminals
- Easy to mount with one screw

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			40	μA
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1,5	mA
V_F	forward voltage drop	$I_F = 10\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,05	V
		$I_F = 30\text{ A}$				1,25	V
		$I_F = 10\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0,94	V
		$I_F = 30\text{ A}$				1,21	V
I_{DAV}	bridge output current	$T_C = 85^{\circ}\text{C}$ rectangular $d = \frac{1}{3}$	$T_{VJ} = 150^{\circ}\text{C}$			20	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0,77	V
r_F	slope resistance					14,2	m Ω
R_{thJC}	thermal resistance junction to case					8	K/W
R_{thCH}	thermal resistance case to heatsink				1		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				15	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			380	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			410	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			325	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			350	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			720	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			700	A ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			530	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			510	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			10		pF

Package FO-B				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I _{RMS}	<i>RMS current</i>	per terminal				100	A
T _{VJ}	<i>virtual junction temperature</i>			-40		150	°C
T _{op}	<i>operation temperature</i>			-40		125	°C
T _{stg}	<i>storage temperature</i>			-40		125	°C
Weight					20		g
M _D	<i>mounting torque</i>			1,8		2,2	Nm
d _{Spp/App}	<i>creepage distance on surface striking distance through air</i>	<i>terminal to terminal</i>	9,0	7,0			mm
d _{Spb/Apb}		<i>terminal to backside</i>	10,0	10,0			mm
V _{ISOL}	<i>isolation voltage</i>	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		3000		V
		t = 1 minute			2500		V

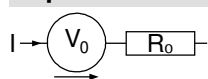


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO25-12NO8	VUO25-12NO8	Box	50	465100

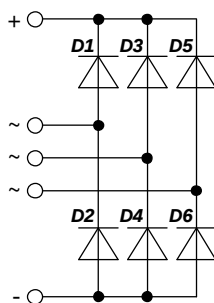
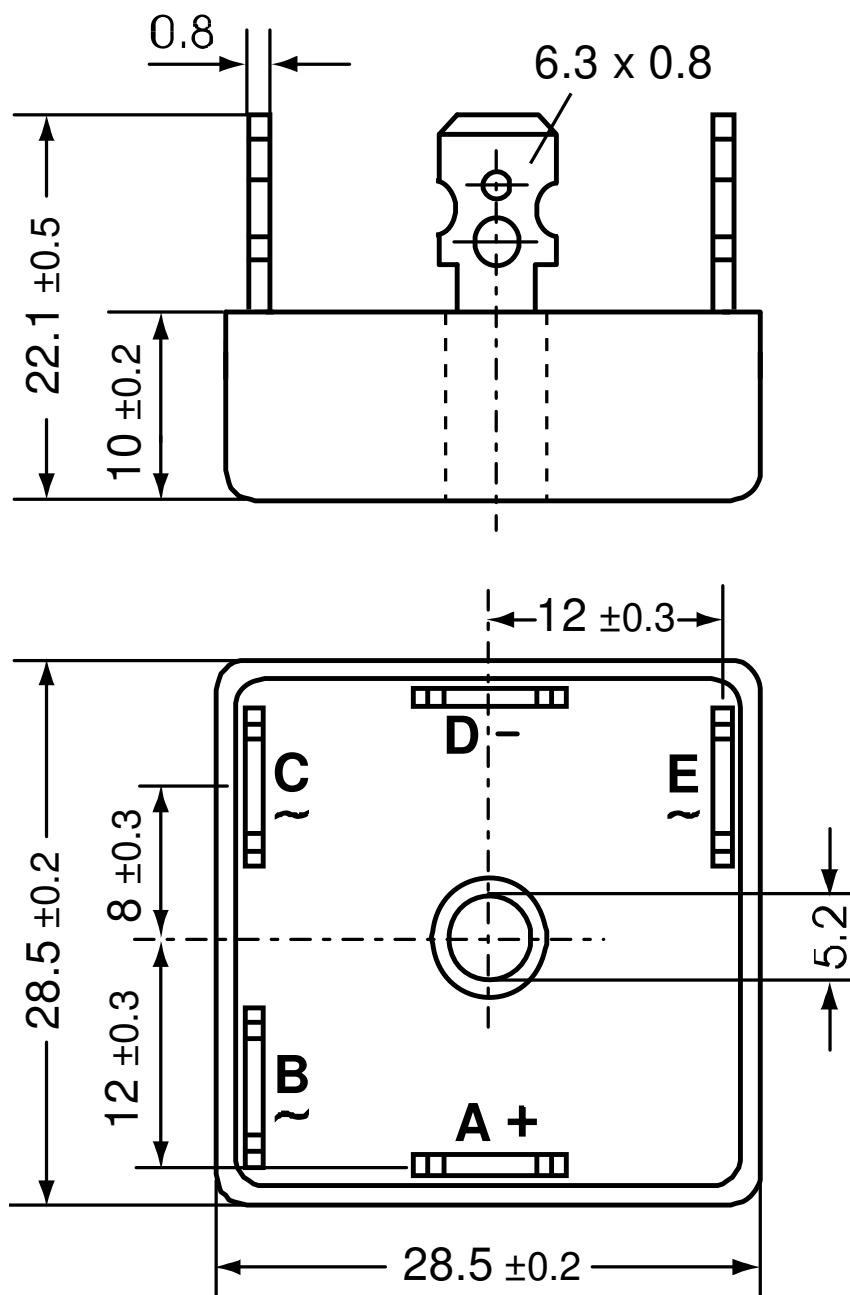
Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$

		Rectifier	
$V_{0\text{ max}}$	<i>threshold voltage</i>	0,77	V
$R_{0\text{ max}}$	<i>slope resistance *</i>	13	mΩ

Outlines FO-B



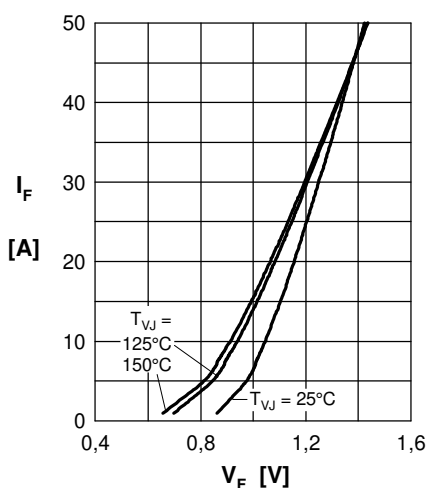
Rectifier


Fig. 1 Forward current vs. voltage drop per diode

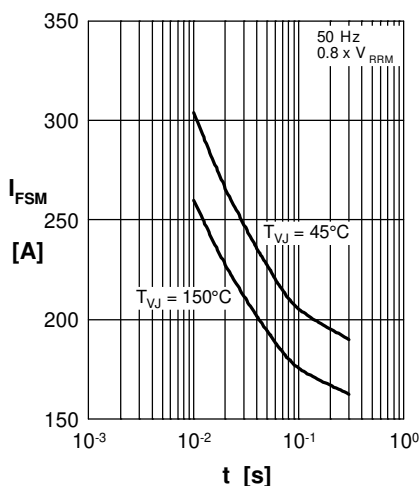


Fig. 2 Surge overload current vs. time per diode

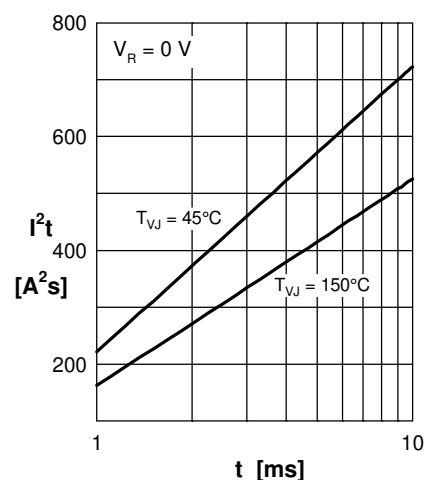


Fig. 3 I^2t vs. time per diode

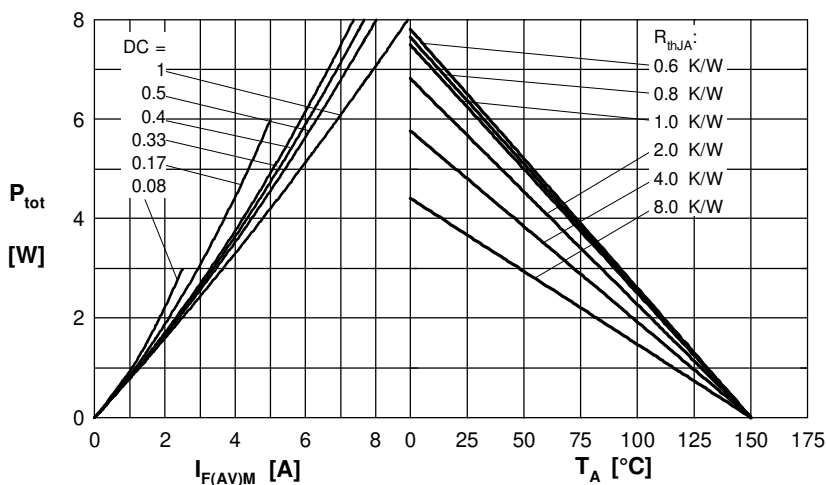


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

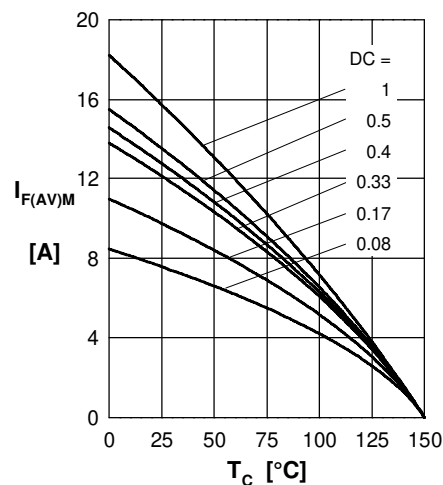


Fig. 5 Max. forward current vs. case temperature per diode

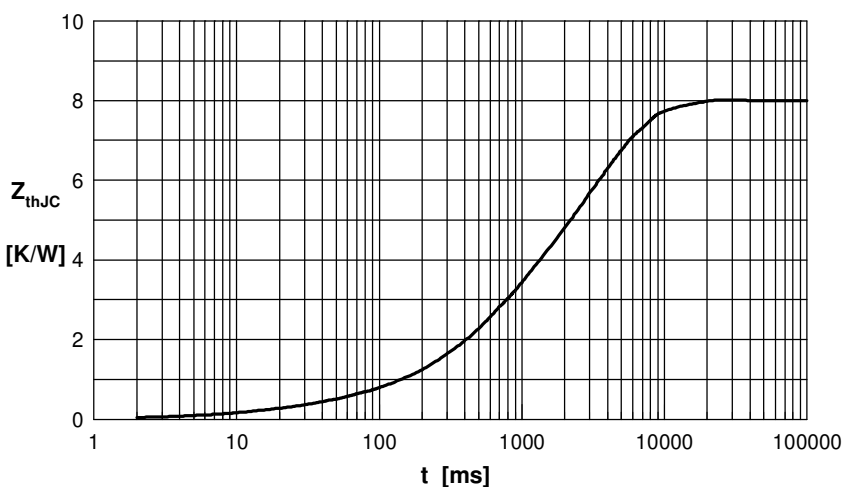


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.040	0.005
2	0.250	0.030
3	1.810	0.500
4	5.900	3.200